

DSC3G03

Silicon NPN epitaxial planar type

For high-frequency amplification
DSC5G03 in SSSMini3 type package

■ Features

- High transition frequency f_T
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C6

■ Packaging

DSC3G0300L Embossed type (Thermo-compression sealing): 10000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

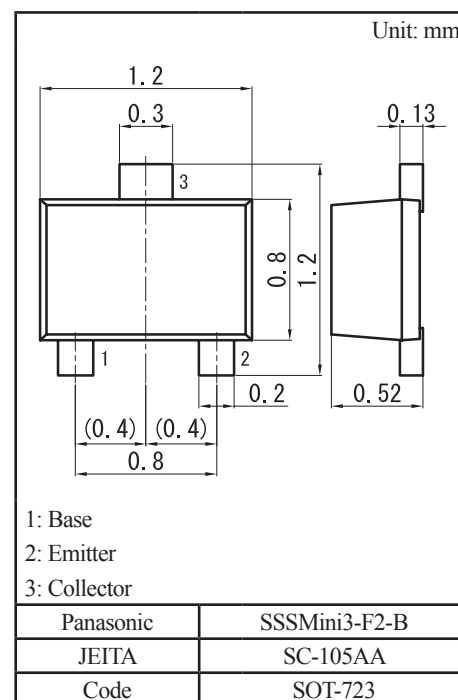
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	30	V
Collector-emitter voltage (Base open)	V_{CEO}	20	V
Emitter-base voltage (Collector open)	V_{EBO}	3	V
Collector current	I_{C}	50	mA
Collector power dissipation	P_{C}	100	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Operating ambient temperature	T_{opr}	-40 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

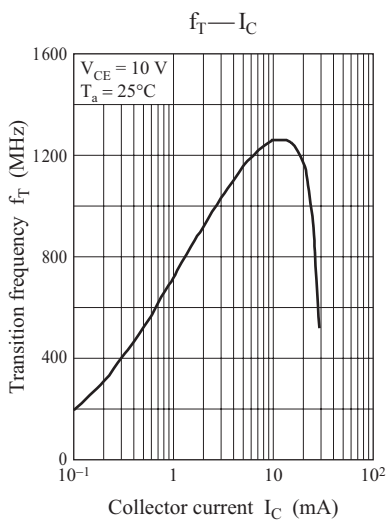
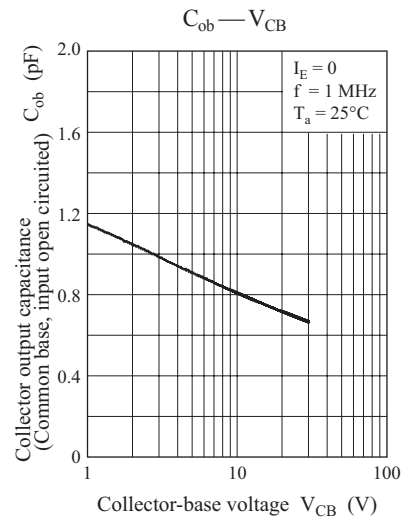
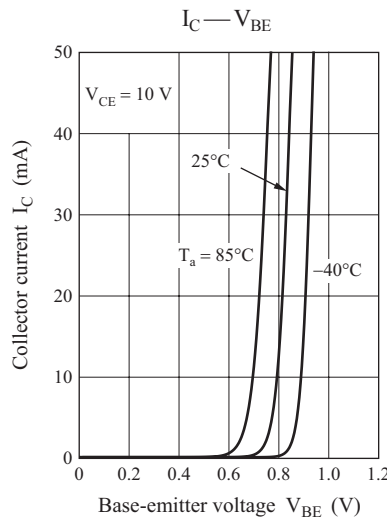
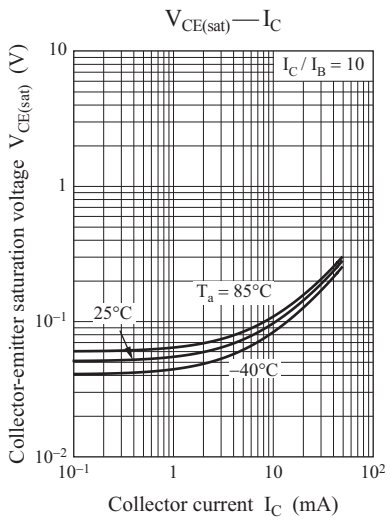
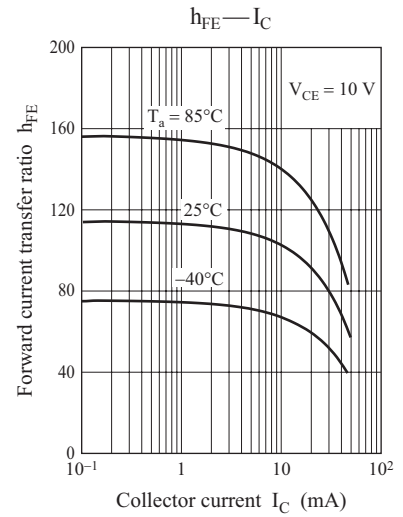
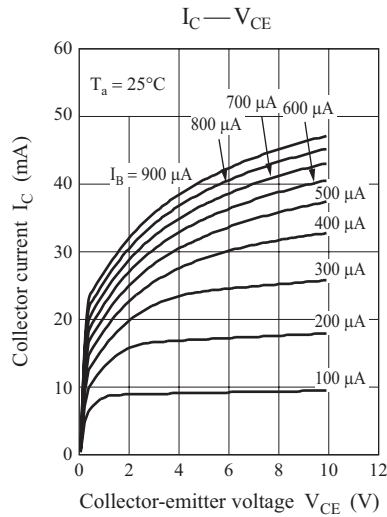
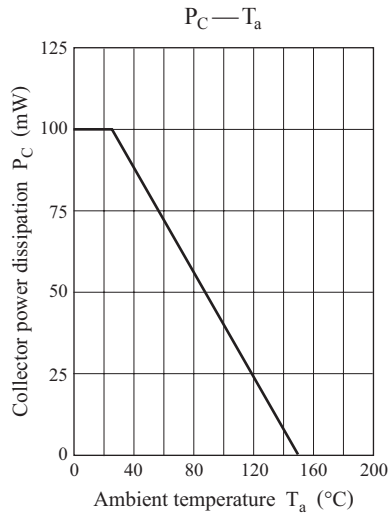
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\text{C}} = 100 \mu\text{A}, I_{\text{E}} = 0$	30			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\text{E}} = 10 \mu\text{A}, I_{\text{C}} = 0$	3			V
Base-emitter voltage	V_{BE}	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 2 \text{mA}$		740		mV
Forward current transfer ratio	h_{FE}	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 2 \text{mA}$	25		250	—
Transition frequency ^{*1}	f_{T}	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 15 \text{mA}$	800		1600	MHz
Reverse transfer capacitance (Common emitter)	C_{re}	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 1 \text{mA}, f = 10.7 \text{MHz}$		0.9		pF
Reverse transfer capacitance (Common base)	C_{rb}	$V_{\text{CB}} = 6 \text{V}, I_{\text{C}} = 0, f = 1 \text{MHz}$		0.7		pF
Power gain	PG	$V_{\text{CE}} = 10 \text{V}, I_{\text{C}} = 1 \text{mA}, f = 200 \text{MHz}$		20		dB

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

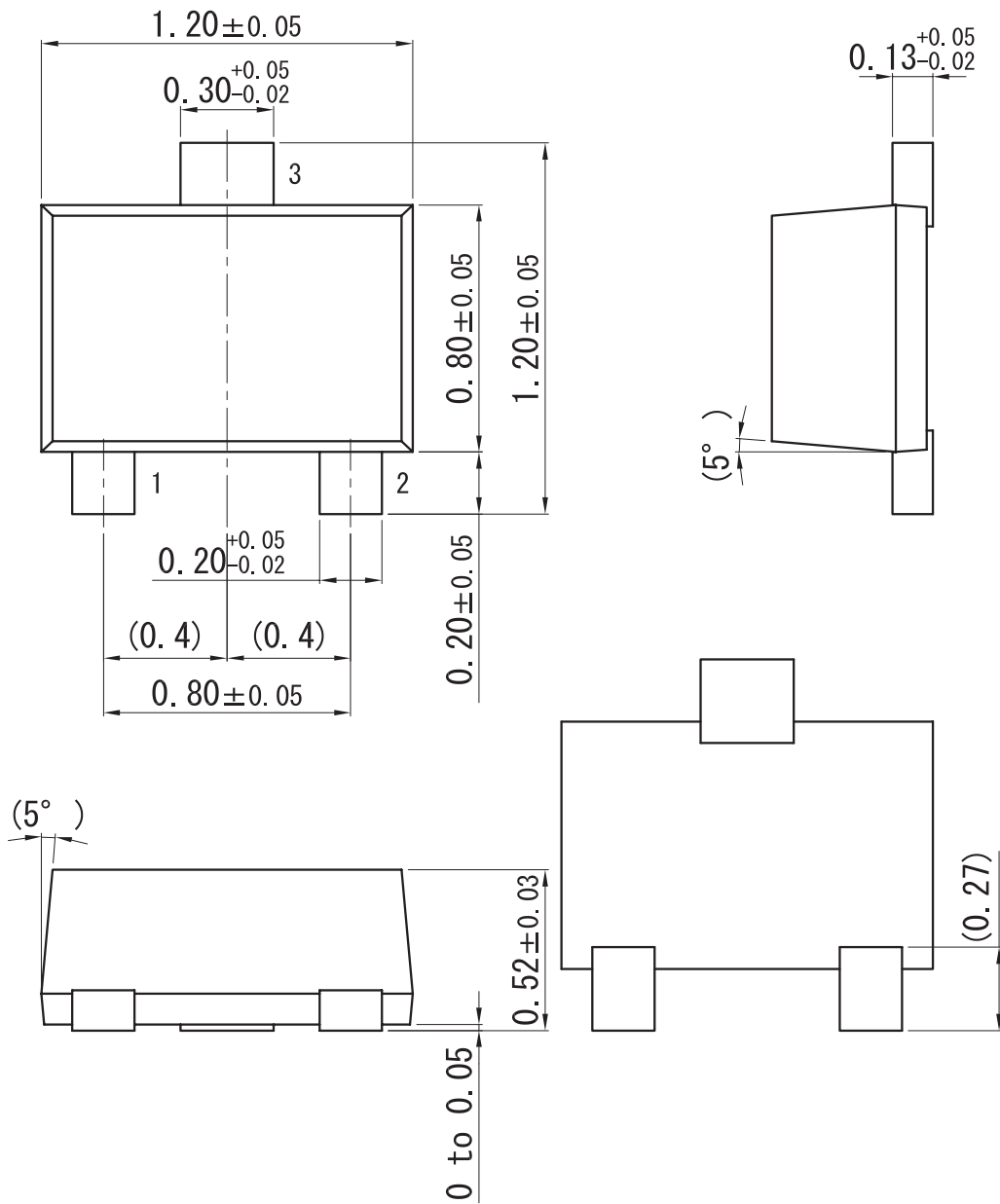
2. *1: Pulse measurement



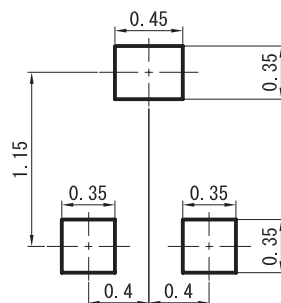


SSSMini3-F2-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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